

/ Descriptions

VRW056 硅 PNP 三极管 封装 SOT-23 塑料封装。 Silicon PNP transistor in a SOT-23 Plastic Package.

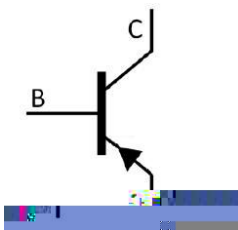
/ Features

饱和压降小， h_{FE} 线性好， h_{FE} 高。

Low saturation voltage, excellent h_{FE} linearity and high h_{FE} .

音频放大器输出级，电压调节器，DC-DC 转换器及继电器驱动。

Output stage of audio amplifier, voltage regulator, DC-DC converter and relay driver.



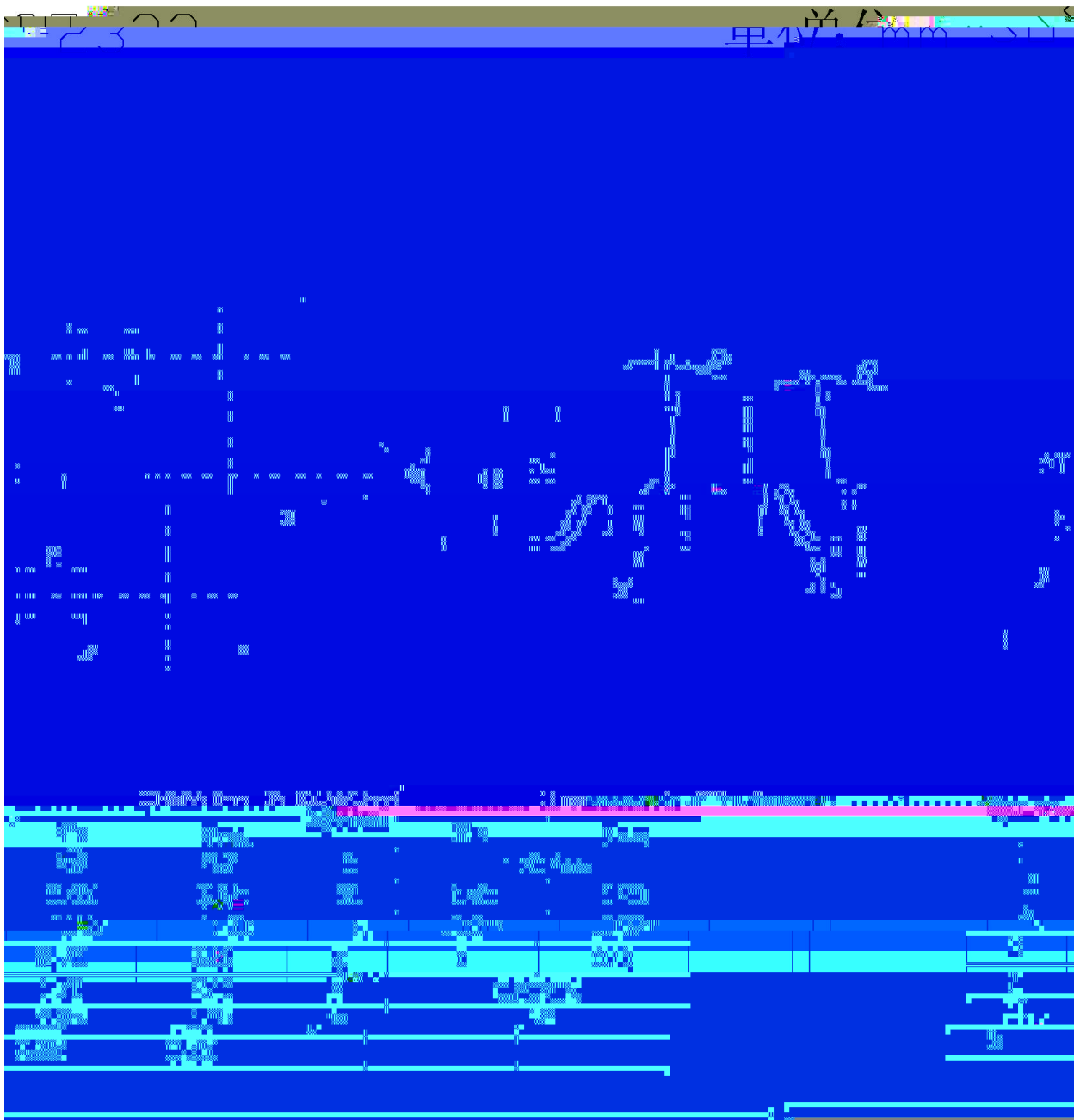
PIN1 基极 PIN 2 发射极 PIN 3 集电极

/ h_{FE} Classifications & Marking

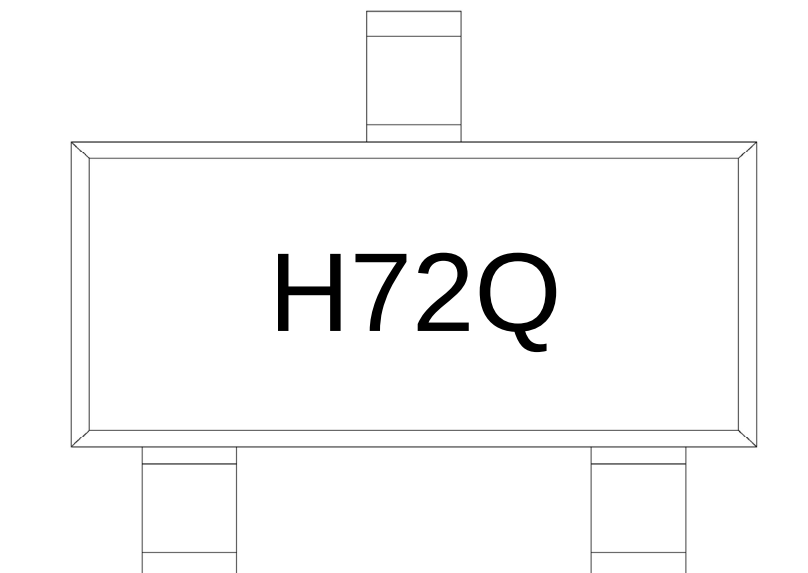
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-30	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current - DC	I_C	-3	A
Collector Current - Pulse	I_{CP}	-7	A
Collector Power Dissipation	P_C	350	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55 ~ 150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -100\mu A$ $I_E = 0$	-40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -1.0mA$ $I_B = 0$	-30			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E = -100\mu A$ $I_C = 0$	-5			V

/ Package Dimensions



/ Marking Instructions



б " X

K X № 3¹ П

:5 X № 3^N П

T X № 6 К П

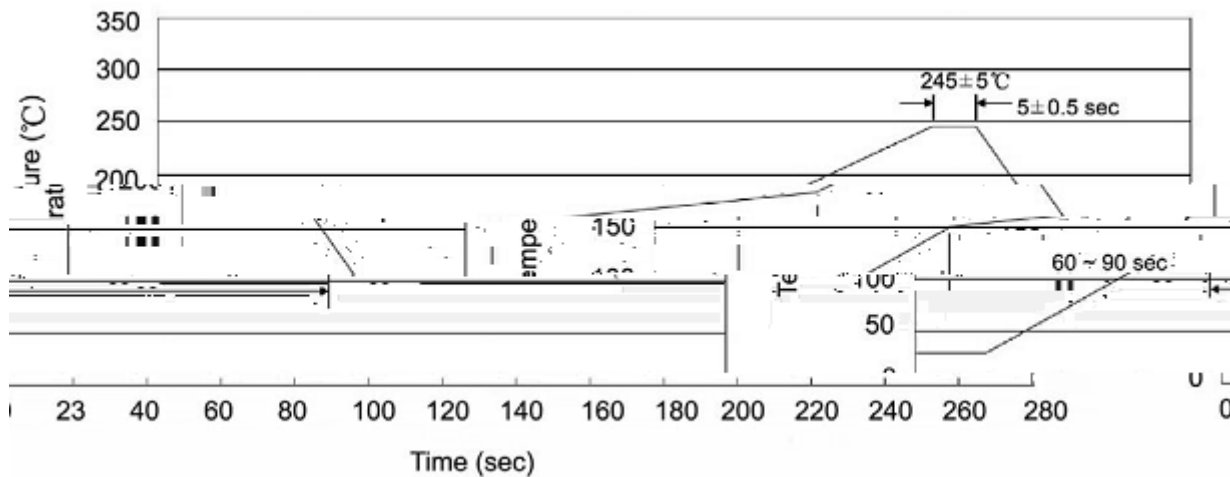
Note:

H: Company Code

72: Product Type Code

Q: h_{FE} Classifications Symbol Code

() / Temperature Profile for IR Reflow Soldering(Pb-Free)



注意:

1. 预加热: 25~150 °C, Time: 60~90sec;
2. 峰值温度: 245±5 °C, Duration: 5±0.5sec;
3. 冷却速度: 2~10 °C/sec.

Note:

1. Preheating: 25~150 °C, Time: 60~90sec.
2. Peak Temp.: 245±5 °C, Duration: 5±0.5sec.
3. Cooling Speed: 2~10 °C/sec.

/ Resistance to Soldering Heat Test Conditions

□ 温度: 260±5 °C, Time: 10±1 sec. Temp.: 260±5 °C Time: 10±1 sec

/ Packaging SPEC.

包装形式: REEL

Package Type	Units					Dimension (unit: mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
SOT-23	3,000	10	30,000	6	180,000	7 ϕ × 8	180×120×180	390×385×205

/ Notices